# **Quad 2-Channel Multiplexer**

## With 5 V-Tolerant Inputs

The MC74LVX157 is an advanced high speed CMOS quad 2-channel multiplexer. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

It consists of four 2-input digital multiplexers with common select (S) and enable  $(\overline{E})$  inputs. When  $\overline{E}$  is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the I0 n or I1 n inputs get routed to the corresponding Z n outputs.

### **Features**

- High Speed:  $t_{PD} = 5.1 \text{ ns (Typ)}$  at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant

## **PIN NAMES**

Pins	Function
I0n	Source 0 Data Inputs
l1n	Source 1 Data Inputs
Ē	Enable Input
S	Select Input
Zn	Outputs

## TRUTH TABLE

	INP	UTS	OUTPUT	
Ē	S	l0n	l1n	Zn
Н	Х	Х	Х	L
L	Н	Х	L	L
L	Н	Х	Н	Н
L	L	L	Χ	L
L	L	Н	Χ	Н

H = High Voltage Level; L = Low Voltage Level; X = High or Low Voltage Level ; For I $_{\rm CC}$  Reasons DO NOT FLOAT Inputs



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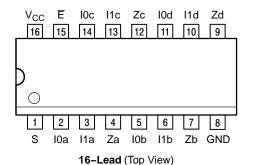
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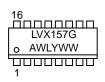


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

## **PIN ASSIGNMENT**



## **MARKING DIAGRAMS**





SOIC-16

TSSOP-16

LVX157 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

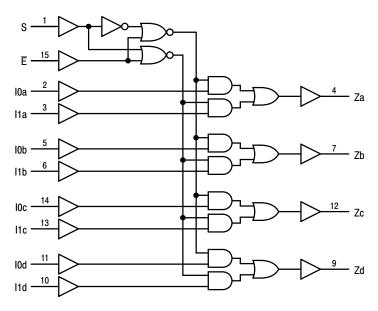


Figure 1. Logic Diagram

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>out</sub>	DC Output Voltage	–0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	Output Diode Current	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation	180	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	7	T <sub>A</sub> = 25°C		$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4	- - -	- - -	1.5 2.0 2.4	- - -	V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6	- - -	- - -	0.5 0.8 0.8	- - -	0.5 0.8 0.8	V
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$\begin{split} I_{OH} &= -50 \mu A \\ I_{OH} &= -50 \mu A \\ I_{OH} &= -4 m A \end{split}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0	- - -	1.9 2.9 2.48	- - -	V
V <sub>OL</sub>	Low-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$\begin{split} I_{OL} &= 50 \mu A \\ I_{OL} &= 50 \mu A \\ I_{OL} &= 4 m A \end{split}$	2.0 3.0 3.0	- - -	0.0 0.0 -	0.1 0.1 0.36	- - -	0.1 0.1 0.44	V
l <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5V or GND	3.6	-	-	±0.1	-	±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6	-	_	4.0	-	40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$ )

				1	T <sub>A</sub> = 25°(	:	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, Input to Output	V <sub>CC</sub> = 2.7V	$C_L = 15pF$ $C_L = 50pF$	-	6.6 9.1	12.5 16.0	1.0 1.0	15.5 19.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	-	5.1 7.6	7.9 11.4	1.0 1.0	9.5 13.0	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, S to Zn	V <sub>CC</sub> = 2.7V	$C_L = 15pF$ $C_L = 50pF$	-	8.9 11.4	16.9 20.4	1.0 1.0	20.5 24.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	-	7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, E to Zn	V <sub>CC</sub> = 2.7V	$C_L = 15pF$ $C_L = 50pF$	-	9.1 11.6	17.6 21.1	1.0 1.0	20.5 24.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	-	7.2 9.7	11.5 15.0	1.0 1.0	13.5 17.0	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50pF$ $C_L = 50pF$	-	_	1.5 1.5	- -	1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

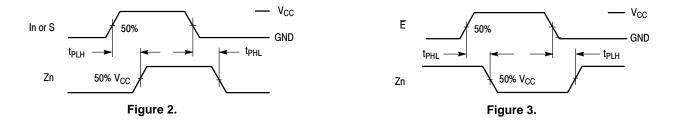
## **CAPACITIVE CHARACTERISTICS**

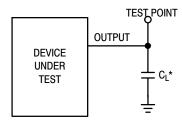
		T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance	-	4	10	-	10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)	1	20	-	ı	1	pF

C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per bit). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## $\textbf{NOISE CHARACTERISTICS} \text{ (Input } t_{\text{f}} = t_{\text{f}} = 3.0 \text{ns, } C_{\text{L}} = 50 \text{pF, } V_{\text{CC}} = 3.3 \text{V, Measured in SOIC Package)}$

		T <sub>A</sub> =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage	_	2.0	V
$V_{ILD}$	Maximum Low Level Dynamic Input Voltage	_	0.8	V





\*Includes all probe and jig capacitance

Figure 4. Propagation Delay Test Circuit

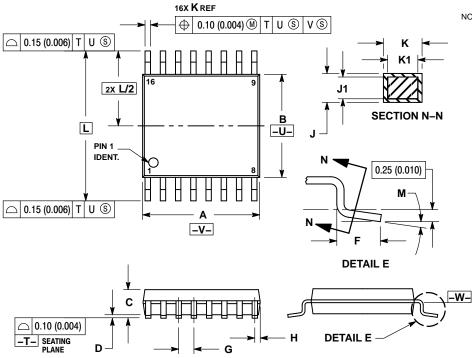
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MC74LVX157DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel	
MC74LVX157DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

## TSSOP-16 CASE 948F **ISSUE B**



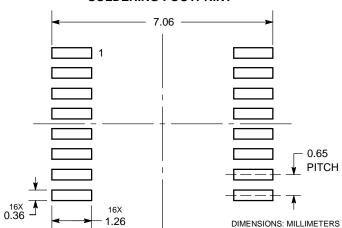
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS.

  - FLASH. PROTRUSIONS OR GATE BURRS.
    MOLD FLASH OR GATE BURRS SHALL NOT
    EXCEED 0.15 (0.006) PER SIDE.
    4. DIMENSION B DOES NOT INCLUDE
    INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION SHALL
    NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08
    (0.003) TOTAL IN EXCESS OF THE K
    DIMENSION AT MAXIMUM MATERIAL
    CONDITION. CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR

  - 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0°	8°	0°	8°	

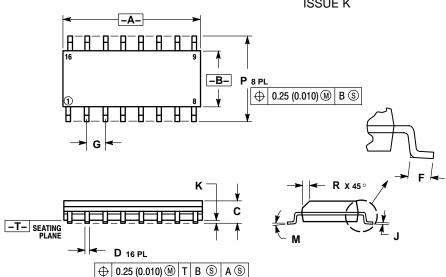
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **PACKAGE DIMENSIONS**

## SOIC-16 CASE 751B-05 ISSUE K



#### NOTES:

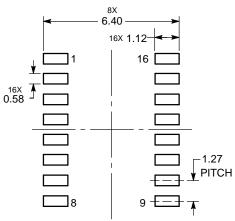
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD
- DIMENSIONS A AND B DO NOT INCLUDE MOLE PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR
   PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

 MILLIMETERS NICLES

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

### SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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